

INFORMATION DISCLOSURE CITATION
(Not to be filled in by the applicant)

Serial Number (Optional)

FTS920030571051

Application Number

10/708,378

Applicant

Shu, et al.

Filing Date

2-23-04

Group Art Unit

2618

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBJECT AREA	RELEVANCE (1-5) (1=NOT RELEVANT)
h		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leoty			
		5,851,651	1-19-99	Bravon, et al.			
		5,880,040	3-9-99	Sun, et al.			
h		5,940,716	8-17-99	Jin, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBJECT AREA	RELEVANCE (1-5) (1=NOT RELEVANT)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBJECT AREA	Relevance	
							YES	NO

OTHER DOCUMENTS (Including Abstracts, Tolls, Data, Preliminary Pages, Etc.)

h		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing," Pp. 14-15. Date is not available.
h		Z. Yang, et al., "Anomalous Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors," Pp. 1-5. Date is not available.

EXAMINER

My [Signature] My [Signature]

DATE CONSIDERED

8-15-05

EXAMINER: Initial if citation considered, whether or not citation is in conformity with MPEP Section 609. Draw line through checkbox if not in conformity and not considered. Include copy of this form with oral communication to applicant.

INFORMATION DISCLOSURE CITATION
(Disclosures from examination)

Document Number (Optional)

FES920039371961

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Applicant(s)

Zhu, et al.

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2-27-94

Group Art(s)

2618

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	RELEVANCE IF APPROPRIATE
pm		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schettina			
pm		5,679,565	10-21-97	Schettina			

U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	RELEVANCE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Page(s), etc.)*

pm	U.S. Monroe, et al., "Temperature Dependence of Emitter-Base Reverse Bias Degradation and its Mechanism Analyzed by MOS Structures," Paper #2, pp. 146-147, <i>IEEE</i> , 1969
pm	C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors," <i>IEEE 1991 Bipolar Circuits and Technology Meeting</i> 7-5, pp. 170-173.

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